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AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A group III nitride compound semiconductor light-emitting device, comprising:
 - a semiconductor laminate portion including a light-emitting layer; and
 - a reflection surface disposed so as to be opposite to a side surface of said light-emitting layer,
wherein said semiconductor laminate portion and said reflection surface are provided on in the same chip.
2. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface reflects light emitted from said side surface of said semiconductor laminate portion into a direction of an optical axis of said light-emitting device.
3. (Original) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of from 0.1 to 10 μ m.
4. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a material which is the same as that of an n pad electrode.
5. (Original) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein a portion of said n pad electrode opposite to said side surface of said semiconductor laminate portion forms a second reflection surface.
6. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed on an n-type semiconductor layer which is formed by etching to a first depth, and said n pad electrode is

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formed on said n-type semiconductor layer which is formed by etching to a second depth shallower than said first depth.

7. (Original) A group II nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed integrally with said n pad electrode.
8. (Previously presented) A group III nitride compound semiconductor light-emitting device, comprising:
 - a plurality of group III nitride compound semiconductor layers comprising a light-emitting layer;
 - a groove formed in said plurality of group III nitride compound semiconductor layers; and
 - a reflection surface formed on an outer side surface of said groove, said reflection surface being disposed opposite to a side surface of said light-emitting layer.
9. (Original) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein said groove is formed by a dicing saw.
10. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein said reflection surface comprises a metal layer.
11. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 10, wherein said metal layer comprises a material which is the same as that of an n pad electrode, and said metal layer is formed at the same time when said n pad electrode is formed.
12. (Original) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein light emitted from a side surface of said laminate is reflected by said reflected surface in a direction of an optical axis of said light-emitting device.

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13. (Previously presented) A group nitride compound semiconductor light-emitting device according to claim 8, wherein said plurality of group III nitride compound semiconductor layers further comprises a substrate, a bottom of said groove being defined by said substrate.
14. (Original) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein said groove is substantially parallel to a chip cutting line.
15. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of 0.2 μm to 7 μm .
16. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of 0.3 μm to 5 μm .
17. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface is formed on a layer in said semiconductor laminate portion.
18. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein an upper surface of said reflection surface is elevated higher than said light-emitting layer.
19. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a curved reflection surface.
20. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein a width of said groove is in a range of 3 μm to 50 μm .

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21. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein a width of said groove is in a range of 7 μm to 40 μm .

22. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein at least a portion of said reflector surface lies in a same plane as a portion of said light-emitting layer.